

Product data sheet

1. General description

Dual N-channel enhancement mode Field-Effect Transistor (FET) in a very small SOT363 (TSSOP6) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. Features and benefits

- Low threshold voltage
- Very fast switching
- Trench MOSFET technology
- ElectroStatic Discharge (ESD) protection > 2 kV HBM

3. Applications

- · Relay driver
- High-speed line driver
- Low-side loadswitch
- Switching circuits

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transis	tor						
V _{DS}	drain-source voltage	T _j = 25 °C		-	-	30	V
V_{GS}	gate-source voltage	-		-12	-	12	V
I _D	drain current	V _{GS} = 4.5 V; T _{amb} = 25 °C; t ≤ 5 s	[1]	-	-	0.95	Α
Static char	acteristics (per transistor)						
R _{DSon}	drain-source on-state resistance	$V_{GS} = 4.5 \text{ V}; I_D = 0.9 \text{ A}; T_j = 25 ^{\circ}\text{C}$		-	211	252	mΩ

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².



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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S1	source TR1	<u>654</u>	D1 D2
2	G1	gate TR1		
3	D2	drain TR2	0	G1 $G2$ $G2$
4	S2	source TR2	☐1 ☐2 ☐3	
5	G2	gate TR2	TSSOP6 (SOT363)	
6	D1	drain TR1		S1 S2 017aaa256

6. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
PMGD175XNE	TSSOP6	plastic surface-mounted package; 6 leads	SOT363			

7. Marking

Table 4. Marking codes

Type number	Marking code
	[1]
PMGD175XNE	LU%

[1] % = placeholder for manufacturing site code

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8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
Per transis	tor					
V _{DS}	drain-source voltage	T _j = 25 °C		-	30	V
V_{GS}	gate-source voltage			-12	12	V
I _D	drain current	$V_{GS} = 4.5 \text{ V}; T_{amb} = 25 ^{\circ}\text{C}; t \le 5 \text{ s}$	[1]	-	0.95	Α
		V _{GS} = 4.5 V; T _{amb} = 25 °C	[1]	-	0.87	Α
		V _{GS} = 4.5 V; T _{amb} = 100 °C	[1]	-	0.5	Α
I _{DM}	peak drain current	T_{amb} = 25 °C; single pulse; $t_p \le 10 \mu s$		-	4	Α
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2]	-	260	mW
			[1]	-	310	mW
		T _{sp} = 25 °C		-	905	mW
Per device						
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2]	-	390	mW
Tj	junction temperature			-55	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C
Source-dra	in diode		'	'	'	,
Is	source current	T _{amb} = 25 °C	[1]	-	0.31	Α

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².

^[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

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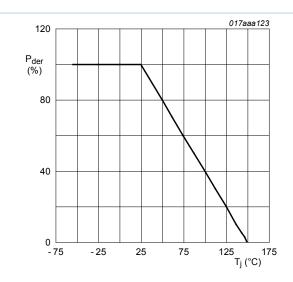


Fig. 1. Normalized total power dissipation as a function of junction temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

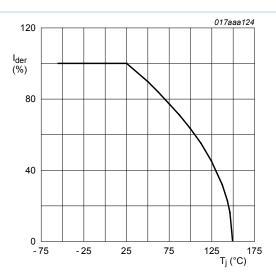


Fig. 2. Normalized continuous drain current as a function of junction temperature

$$I_{der} = \frac{I_D}{I_{D(25^{\circ}C)}} \times 100 \%$$

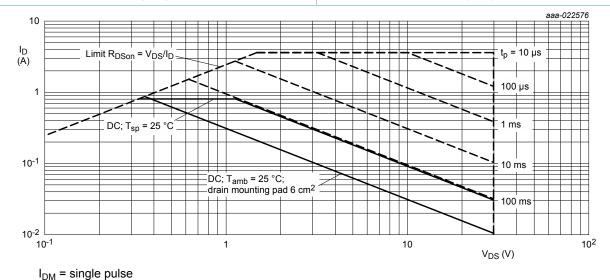


Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drainsource voltage

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9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit		
Per transistor									
ung a)	thermal resistance	in free air	[1]	-	417	480	K/W		
	from junction to ambient		[2]	-	352	405	K/W		
	ambient	in free air; t ≤ 5 s	[2]	-	295	340	K/W		
$R_{th(j-sp)}$	thermal resistance from junction to solder point			-	120	138	K/W		
Per device									
$R_{\text{th(j-a)}}$	thermal resistance from junction to ambient	in free air	[1]	-	-	320	K/W		

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm².

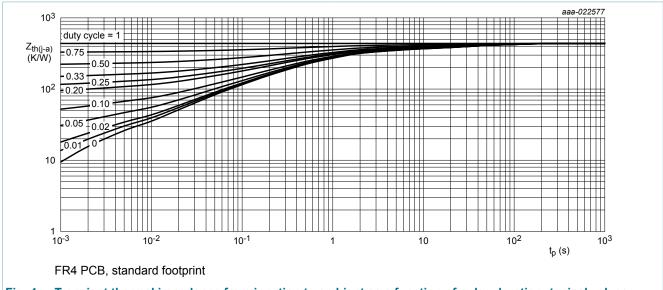
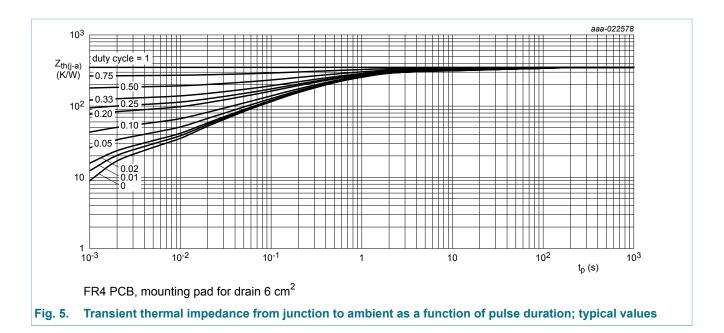


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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10. Characteristics

Table 7 Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics (per transistor)					
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	30	-	-	V
V_{GSth}	gate-source threshold voltage	$I_D = 250 \ \mu\text{A}; \ V_{DS} = V_{GS}; \ T_j = 25 \ ^{\circ}\text{C}$	0.75	1	1.25	V
I _{DSS}	drain leakage current	$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	1	μA
I _{GSS}	gate leakage current	V _{GS} = 12 V; V _{DS} = 0 V; T _j = 25 °C	-	-	10	μA
		V _{GS} = -12 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-10	μA
		V _{GS} = 4.5 V; V _{DS} = 0 V; T _j = 25 °C	-	-	5	μA
		V_{GS} = -4.5 V; V_{DS} = 0 V; T_j = 25 °C	-	-	-5	μA
R _{DSon} drain-source on-state resistance	drain-source on-state	V_{GS} = 4.5 V; I_{D} = 0.9 A; T_{j} = 25 °C	-	211	252	mΩ
	resistance	V _{GS} = 4.5 V; I _D = 0.9 A; T _j = 150 °C	-	344	411	mΩ
	V_{GS} = 2.5 V; I_D = 0.8 A; T_j = 25 °C	-	267	319	mΩ	
9 _{fs}	forward transconductance	$V_{DS} = 10 \text{ V}; I_D = 0.9 \text{ A}; T_j = 25 \text{ °C}$	-	3.5	-	S
Dynamic ch	naracteristics (per transist	or)				
Q _{G(tot)}	total gate charge	$V_{DS} = 15 \text{ V}; I_D = 0.9 \text{ A}; V_{GS} = 4.5 \text{ V};$	-	1.05	1.65	nC
Q_{GS}	gate-source charge	T _j = 25 °C	-	0.15	-	nC
Q_{GD}	gate-drain charge		-	0.27	-	nC
C _{iss}	input capacitance	V _{DS} = 15 V; f = 1 MHz; V _{GS} = 0 V;	-	81	-	pF
C _{oss}	output capacitance	T _j = 25 °C	-	13	-	pF
C _{rss}	reverse transfer capacitance		-	9	-	pF
t _{d(on)}	turn-on delay time	V_{DS} = 15 V; I_{D} = 0.9 A; V_{GS} = 4.5 V;	-	7	-	ns
t _r	rise time	$R_{G(ext)} = 6 \Omega$; $T_j = 25 °C$	-	14	-	ns
t _{d(off)}	turn-off delay time		-	17	-	ns
t _f	fall time		-	6	-	ns
Source-drai	in diode (per transistor)		'			
V_{SD}	source-drain voltage	$I_S = 0.3 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$	-	0.7	1.2	V
		- I				

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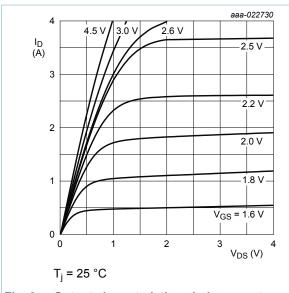
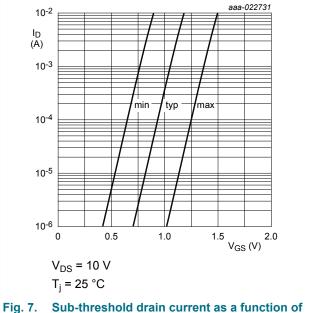
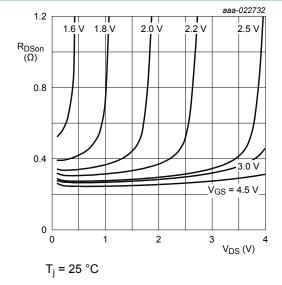


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values



Sub-threshold drain current as a function of



Drain-source on-state resistance as a function Fig. 8. of drain current; typical values

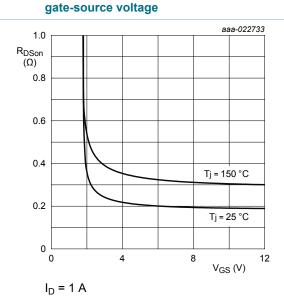


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

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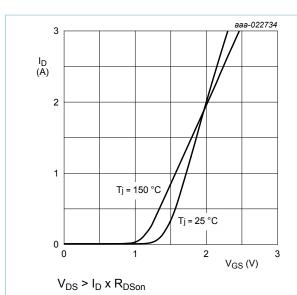


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

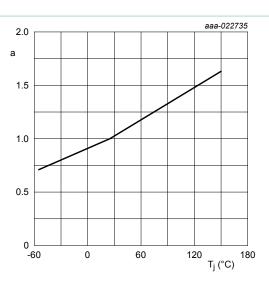


Fig. 11. Normalized drain-source on-state resistance as a function of ambient temperature; typical values

$$a = \frac{R_{DSon}}{R_{DSon(25\,^{\circ}C)}}$$

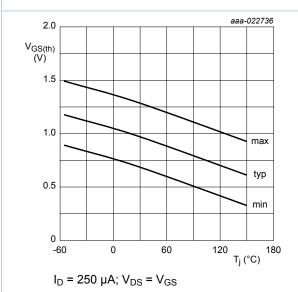
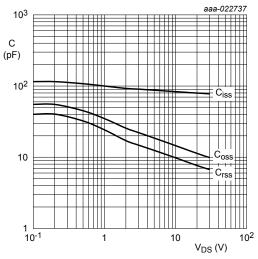


Fig. 12. Gate-source threshold voltage as a function of ambient temperature



 $f = 1 MHz; V_{GS} = 0 V$

Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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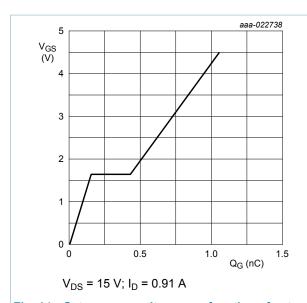


Fig. 14. Gate-source voltage as a function of gate charge; typical values

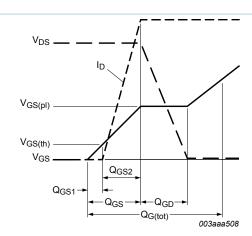


Fig. 15. Gate charge waveform definitions

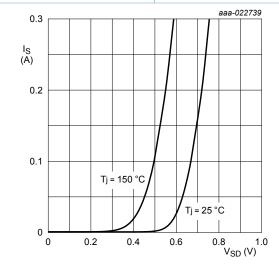
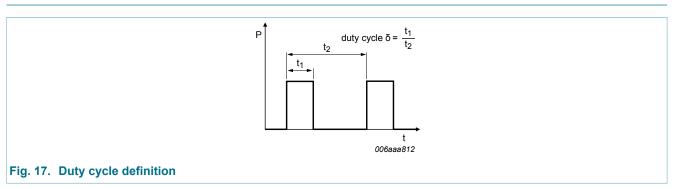


Fig. 16. Source current as a function of source-drain voltage; typical values

11. Test information

 $V_{GS} = 0 V$



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12. Package outline

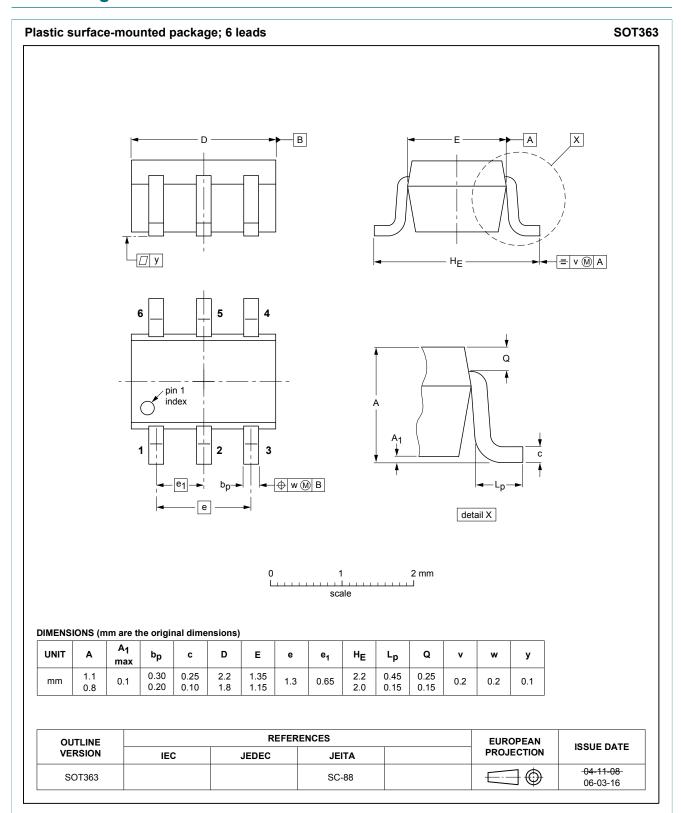


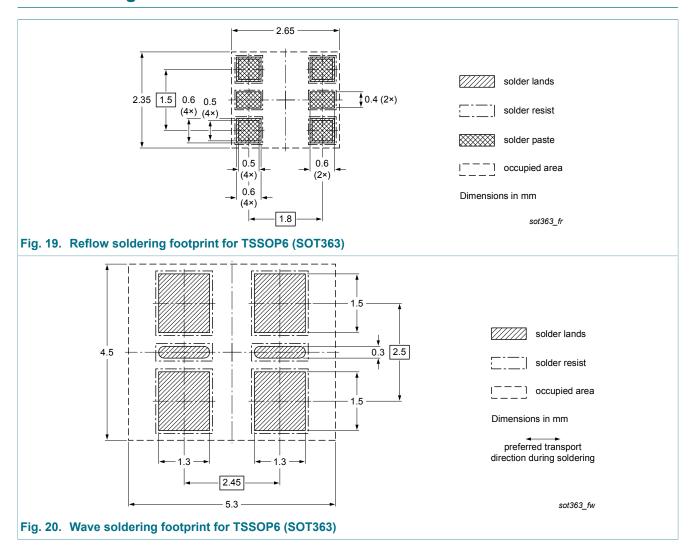
Fig. 18. Package outline TSSOP6 (SOT363)

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13. Soldering



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14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMGD175XNE v.1	20160415	Product data sheet	-	-

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15. Legal information

15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
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